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Course Name - - Power Electronics Course Code - DECE605C

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M.SC.CS)	
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M.SC.(MN	M)
B.A.(Eng)	
Answer all the qu	uestions. Each question carry one mark.
. 1.ln a three-ph delta connecte	ase half wave rectifier usually, the primary side of the transformer is ed because
Mark only one	oval.
it has no r	neutral connection
we can ge	et greater output voltage
it provides	s a path for the triplen harmonics
it provides	s better temperature stability

10.	2.In a three-phase half wave diode rectifier using 3 diodes, each diode conducts for
	Mark only one oval.
	90 degrees
	120 degrees
	180 degrees
	360 degrees
11.	3.In a three-phase half wave 6-pulse mid-point type diode rectifier, each diode conducts for
	Mark only one oval.
	120°
	60°
	90°
	180
12.	4.A 3-phase bridge rectifier, has the average output voltage as 286.48 V. Find the maximum value of line voltage
	Mark only one oval.
	100 V
	200 V
	300 V
	400 V

13.	5.A 3-phase bridge rectifier charges a 240 V battery. The rectifier is given a 3-phase, 230 V supply. The current limiting resistance in series with the battery is of 8 Ω . Find the average value of battery charging current.
	Mark only one oval.
	12.56 A
	8.82 A
	9.69 A
	6.54 A
14.	6.In a 3-phase full converter using six SCRs, gating circuit must provide
	Mark only one oval.
	one firing pulse every 30°
	one firing pulse every 60°
	one firing pulse every 90°
	three firing pulses per cycle
15.	7.The magnitude of gate voltage and gate current for triggering an SCR is
	Mark only one oval.
	inversely proportional to the temperature
	directly proportional to the temperature
	inversely proportional to the anode current requirement
	directly proportional to the anode current requirement

16.	8.The major function of the pulse transformer is to
	Mark only one oval.
	increase the voltage amplitude
	reduce harmonics
	isolate low & high power circuit
	create periodic pulses
17.	9.A p-type semiconductor material is doped with impurities whereas
	a n-type semiconductor material is doped with impurities
	Mark only one oval.
	acceptor, donor
	dfs algorithm
	donor, donor
	onor, acceptor
18.	10.Which of the below mentioned statements is false regarding a p-n junction diode?
	Mark only one oval.
	Diode are uncontrolled devices
	Diodes are rectifying devices
	Diodes are unidirectional devices
	Diodes have three terminals

19.	11.When a physical contact between a p-region & n-region is established which of the following is most likely to take place?
	Mark only one oval.
	Electrons from N-region diffuse to P-region
	Holes from P-region diffuse to N-region
	Both of the above mentioned statements are true
	Nothing will happen
20.	12.Which of the following is true in case of an unbiased p-n junction diode?
	Mark only one oval.
	Diffusion does not take place
	Diffusion of electrons & holes goes on infinitely
	There is zero electrical potential across the junctions
	Charges establish an electric field across the junctions
0.1	
21.	13.Which of the following is true in case of a forward biased p-n junction diode?
	Mark only one oval.
	The positive terminal of the battery sucks electrons from the p-region
	The positive terminal of the battery injects electrons into the p-region
	The negative terminal of the battery sucks electrons from the p-region
	None of the above mentioned statements are true

22.	14.Power diode is
	Mark only one oval.
	a three terminal semiconductor device
	a two terminal semiconductor device
	a four terminal semiconductor device
	a three terminal analog device
23.	15.The V-I Characteristics of the diode lie in the
	Mark only one oval.
	1st & 2nd quadrant
	1st & 3rd quadrant
	1st & 4th quadrant
	Only in the 1st quadrant
24.	16.Which of the following is true in case of a power diode with R load?
	Mark only one oval.
	I grows almost linearly with V
	I decays almost linearly with V
	I initial grows than decays
	I is independent of V

25.	17.In case of an ideal power diode, the leakage current flows from
	Mark only one oval.
	anode to cathode
	cathode to anode
	in both the directions
	leakage current does not flow
26.	18.A power diode with small softness factor (S-factor) has
	Mark only one oval.
	small oscillatory over voltages
	large oscillatory over voltages
	large peak reverse current
	small peak reverse current
27.	19.At turn-on the initial delay or turn on delay is the time required for the
	Mark only one oval.
	input inductance to charge to the threshold value
	input capacitance to charge to the threshold value
	input inductance to discharge to the threshold value
	input capacitance to discharge to the threshold value

28	8.	20.Choose the correct statement
		Mark only one oval.
		MOSFET suffers from secondary breakdown problems MOSFET has lower switching losses as compared to other devices MOSFET has high value of on-state resistance as compared to other devices
		All of the mentioned
2	9.	21.Which among the following devices is the most suited for high frequency applications?
		Mark only one oval.
		BJT IGBT
		MOSFET SCR
3	0.	22.For a MOSFET Vgs=3V, Idss=5A, and Id=2A. Find the pinch of voltage Vp
		Mark only one oval.
		4.08
		8.16
		16.32
		0V

31.	23.How does the MOSFET differ from the JFET?
	Mark only one oval.
	JFET has a p-n junction
	They are both the same
	JFET is small in size
	MOSFET has a base terminal
32.	24.The basic advantage of the CMOS technology is that
	Mark only one oval.
	It is easily available
	It has small size
	It has lower power consumption
	It has better switching capabilities
33.	25.The N-channel MOSFET is considered better than the P-channel MOSFET due to its
	Mark only one oval.
	low noise levels
	TTL compatibility
	lower input impedance
	faster operation

34.	26.The arrow on the symbol of MOSFET indicates
	Mark only one oval.
	that it is a N-channel MOSFET the direction of electrons the direction of conventional current flow that it is a P-channel MOSFET
35.	27.In the internal structure of a MOSFET, a parasitic BJT exists between the Mark only one oval.
	source & gate terminals source & drain terminals
	drain & gate terminals
	there is no parasitic BJT in MOSFET
36.	28.In the transfer characteristics of a MOSFET, the threshold voltage is the measure of the Mark only one oval.
	minimum voltage to induce a n-channel/p-channel for conduction minimum voltage till which temperature is constant
	minimum voltage to turn off the device
	none of the above mentioned is true
	Hollo of the above mentioned to trac

37	29. Which of the following devices does not belong to the transistor family?
	Mark only one oval.
	☐ IGBT
	MOSFET
	GT0
	BJT
38	. 30.A power transistor is a
	Mark only one oval.
	three layer, three junction device
	three layer, two junction device
	two layer, one junction device
	four layer, three junction device
39	. 31.In a power transistor, is the controlled parameter.
	Mark only one oval.
	VBE
	VCE
	☐ IB
	☐ IC

40.	32.A power transistor is a device.
	Mark only one oval.
	two terminal, bipolar, voltage controlled
	two terminal, unipolar, current controlled
	merge sortthree terminal, unipolar, voltage controlled
	three terminal, bipolar, current controlled
41.	33.In a power transistor, the IB vs VBE curve is
	Mark only one oval.
	a parabolian exponentially decaying curve
	an exponentially decaying curve
	resembling the diode curve
	a straight line Y = IB
42.	34.The forward current gain a is given by
	Mark only one oval.
	IC/IB
	IC/IE
	IE/IC
	IE/IB

43.	35. The value of β is given by the expression
	Mark only one oval.
	O IC/IB
	IC/IE
	IE/IC
	IE/IB
44.	36.A power BJT is used as a power control switch by biasing it in the cut off region (off state) or in the saturation region (on state). In the on state
	Mark only one oval.
	both the base-emitter & base-collector junctions are forward biased
	the base-emitter junction is reverse biased, and the base collector junction is forward biased
	the base-emitter junction is forward biased, and the base collector junction is reversed biased
	both the base-collector & the base-emitter junctions are reversed biased
45.	37. For a power transistor, if the forward current gain α = 0.97, then β = ?
	Mark only one oval.
	0.03
	2.03
	49.24
	32.33

46.	38.The power electronics devices have a very high efficiency because
	Mark only one oval.
	cooling is very efficient
	the devices traverse active region at high speed & stays at the two states, on and off
	the devices never operate in active region
	the devices always operate in the active region
47.	39. High frequency operation of any device is limited by the
	Mark only one oval.
	forward voltage rating
	switching losses
	thermal conductivity
	heat Sink arrangements
48.	40.Let's say that a transistor is operating at the middle of the load line, then a decrease in the current gain would
	Mark only one oval.
	move the Q point up
	move the Q point down
	result in to & fro motion of the Q point
	not change the Q point

49.	41.IGBT possess
	Mark only one oval.
	low input impedance high input impedance high on-state resistance second breakdown problems
50.	42.IGBT & BJT both posses Mark only one oval. low on-state power losses low switching losses high on-state power losses high input impedance
51.	43.The controlling parameter in IGBT is the Mark only one oval. IG VGE IC VCE

52.	44. In IGBT, the n− layer above the p+ layer is called as the
	Mark only one oval.
	drift layer
	injection layer
	body layer
	collector Layer
53.	45.The major drawback of the first generation IGBTs was that, they had
	Mark only one oval.
	latch-up problems
	noise & secondary breakdown problems
	sluggish operation
	latch-up & secondary breakdown problems
54.	46.A latched up IGBT can be turned off by
	Mark only one oval.
	forced commutation of current
	forced commutation of voltage
	use of a snubber circuit
	none of the mentioned

55.	47.Latch-up occurs in an IGBT when
	Mark only one oval.
	Vce reaches a certain value
	lc reaches a certain value
	Ig reaches a certain value
	the device temperature reaches a certain value
56.	48.The approximate equivalent circuit of an IGBT consists of
	Mark only one oval.
	a BJT & a MOSFET
	a MOSFET & a MCT
	two BJTs
	two MOSFETs
57.	49.An IGBT is also know as
	Mark only one oval.
	MOIGT (Metal oxide insulated gate transistor)
	COMFET (Conductively modulated FET)
	GEMFET (Grain modulated FET)
	all of the mentioned

58.	50.At present, the state-of-the-art semiconductor devices are begin manufactured using
	Mark only one oval.
	Semiconducting Diamond
	Gallium-Arsenide
	Germanium
	Silicon-Carbide
59.	51.A thyristor (SCR) is a
	Mark only one oval.
	P-N-P device
	N-P-N device
	P-N-P-N device
	P-N device
60.	52.Choose the false statement.
	Mark only one oval.
	SCR is a bidirectional device
	SCR is a controlled device
	In SCR the gate is the controlling terminal
	SCR are used for high-power applications

61.	53.The static V-I curve for the SCR is plotted for
	Mark only one oval.
	Ia (anode current) vs Ig (gate current), Va (anode – cathode voltage) as a parameter Ia vs Va with Ig as a parameter
	Va vs Ig with Ia as a parameter
	Ig vs Vg with Ia as a parameter
	Ig vs vg with la as a parameter
62.	54.If the cathode of an SCR is made positive with respect to the anode & no gate current is applied then
	Mark only one oval.
	all the junctions are reversed biased
	all the junctions are forward biased
	only the middle junction is forward biased
	only the middle junction is reversed biased
63.	55.With the anode positive with respect to the cathode & the gate circuit open, the SCR is said to be in the
	Mark only one oval.
	reverse blocking mode
	reverse conduction mode
	forward blocking mode
	forward conduction mode

64.	56.The forward break over voltage is the
	Mark only one oval.
	anode-cathode voltage at which conduction starts with gate signal applied
	anode-cathode voltage at which conduction starts with no gate signal applied
	gate voltage at which conduction starts with no anode-cathode voltage
	gate voltage at which conduction starts with anode-cathode voltage applied
65.	57.A thyristor can be bought from the forward conduction mode to forward blocking mode by
	Mark only one oval.
	the dv/dt triggering method
	applying a negative gate signal
	applying a positive gate signal
	applying a reverse voltage across anode-cathode terminals
66.	58.Usually the forward voltage triggering method is not used to turn-on the SCR because
	Mark only one oval.
	it increases losses
	it causes noise production
	it may damage the junction & destroy the device
	relatively it's an inefficient method

67.	59.Among the following, the most suitable method to turn on the SCR device is the
	Mark only one oval.
	gate triggering method
	dv/dt triggering method
	forward voltage triggering method
	temperature triggering method
68.	60.For the SCR to remain in the ON (conducting) state
	Mark only one oval.
	gate signal is continuously required
	no continuous gate signal is required
	no forward anode-cathode voltage is required
	negative gate signal is continuously required
69.	61.In the reverse blocking mode the middle junction (J2) has the characteristics of that of a
	Mark only one oval.
	transistor
	capacitor
	inductor
	None of above

70.	62.The minimum value of anode current below which it must fall to completely turn-off the device is called as the
	Mark only one oval.
	holding current value
	latching current value
	switching current value
	peak anode current value
71.	63.For effective turning off of the SCR after the anode current has reached zero value,
	Mark only one oval.
	chargers are injected by applying reverse anode-cathode voltage
	chargers are removed by applying reverse anode-cathode voltage
	chargers are injected by applying gate signal
	chargers are removed by applying gate signal
72.	64.The area under the curve of the gate characteristics of thyristor gives the
	Mark only one oval.
	total average gate current
	total average gate voltage
	total average gate impedance
	total average gate power dissipation

73.	65.The average gate power dissipation for an SCR is 0.5 Watts the voltage applied to the gate is Vg = 10 V. What is the maximum value of current lg for safe operation?
	Mark only one oval.
	0.25 A
	10A
	0.05 A
	0.1 A
74.	66.For an SCR, the gate-cathode characteristic has a slop of 130. The gate power dissipation is 0.5 watts. Find Ig
	Mark only one oval.
	0.62 A
	620 Ma
	62 mA
	6.2 mA
75.	67.From the two transistor (T1 & T2) analogy of SCR, the total anode current of SCR is in the equivalent circuit.
	Mark only one oval.
	the sum of both the base currents
	the sum of both the collector current
	the sum of base current of T1 & collector current of T2
	the sum of base current of T2 & collector current of T1

/6.	68.Solid State Relays (SSRs) have a
	Mark only one oval.
	coil and contact arrangement
	optocoupler
	scr
	none of the mentioned
77.	69.TRIAC is used in
	Mark only one oval.
	chopper
	speed control of induction machine
	speed control of universal motor
	none of the mentioned
78.	70.SMPS is used for
	Mark only one oval.
	obtaining controlled ac power supply
	obtaining controlled dc power supply
	storage of dc power
	switch from one source to another

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